## Descriptors Development for Stability Prediction of N-Doped High Entropy Alloy Coatings: A DFT Study

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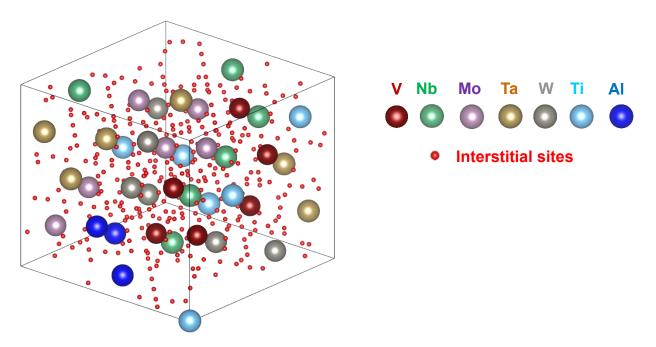


Figure 1: Illustration of a 39-atom HEA (BCC) unit cell, composed of 351 possible interstitial sites, indicating that it is time-consuming to search for a stable and representative N-doped HEA model